

Internally Matched Power GaAs FETs (C-Band)

Features

- High power
 - $P_{1dB} = 36.0$ dBm at 6.4 GHz to 7.2 GHz
- High gain
 - $G_{1dB} = 8.5$ dB at 6.4 GHz to 7.2 GHz
- Broad band internally matched
- Hermetically sealed package

RF Performance Specifications ($T_a = 25^\circ\text{C}$)

Characteristics	Symbol	Condition	Unit	Min.	Typ.	Max
Output Power at 1dB Compression Point	P_{1dB}	$V_{DS} = 10V$ $f = 6.4 \sim 7.2$ GHz	dBm	35.0	36.0	–
Power Gain at 1dB Compression Point	G_{1dB}		dB	7.0	8.0	–
Drain Current	I_{DS}		A	–	1.1	1.5
Power Added Efficiency	η_{add}		%	–	30	–
Channel-Temperature Rise	ΔT_{ch}	$V_{DS} \times I_{DS} \times R_{th(c-c)}$	$^\circ\text{C}$	–	–	80

Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Characteristic	Symbol	Condition	Unit	Min.	Typ.	Max
Trans-conductance	gm	$V_{DS} = 3V$ $I_{DS} = 1.5A$	mS	–	900	–
Pinch-off Voltage	V_{GSoff}	$V_{DS} = 3V$ $I_{DS} = 20mA$	V	-2	-3.5	-5
Saturated Drain Current	I_{DSS}	$V_{DS} = 3V$ $V_{GS} = 0V$	A	–	2.9	3.8
Gate to Source Breakdown Voltage	V_{GSO}	$I_{GS} = -60 \mu A$	V	-5	–	–
Thermal Resistance	$R_{th(c-c)}$	Channel to case	$^\circ\text{C/W}$	–	4.0	6.0

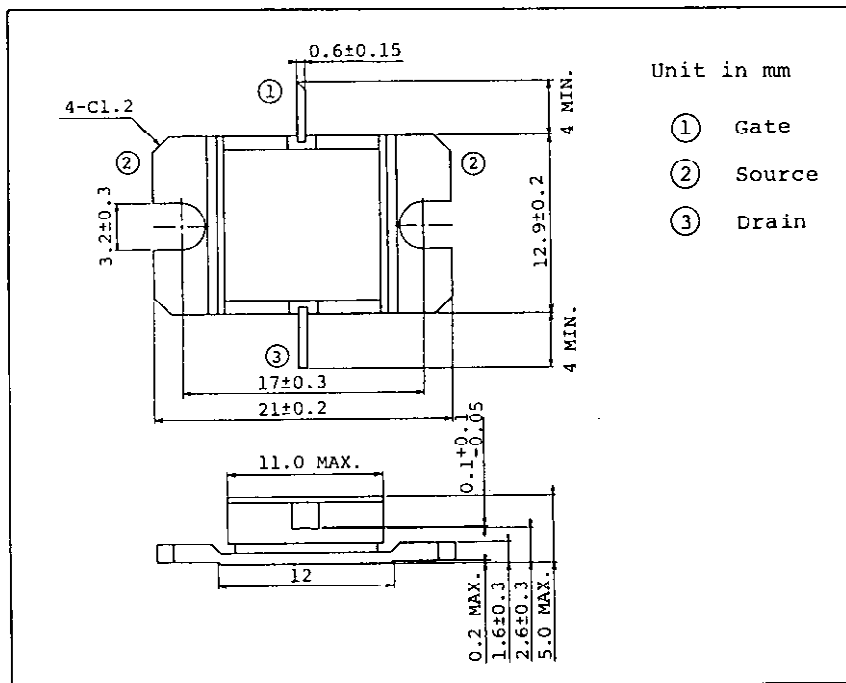
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Absolute Maximum Ratings (T_a = 25° C)

Characteristic	Symbol	Unit	Rating
Drain Source Voltage	V _{DS}	V	15
Gate Source Voltage	V _{GS}	V	-5
Drain Current	I _D	A	4
Total Power Dissipation (T _c = 25°C)	P _T	W	20
Channel Temperature	T _{ch}	°C	175
Storage Temperature	T _{stg}	°C	-65~175

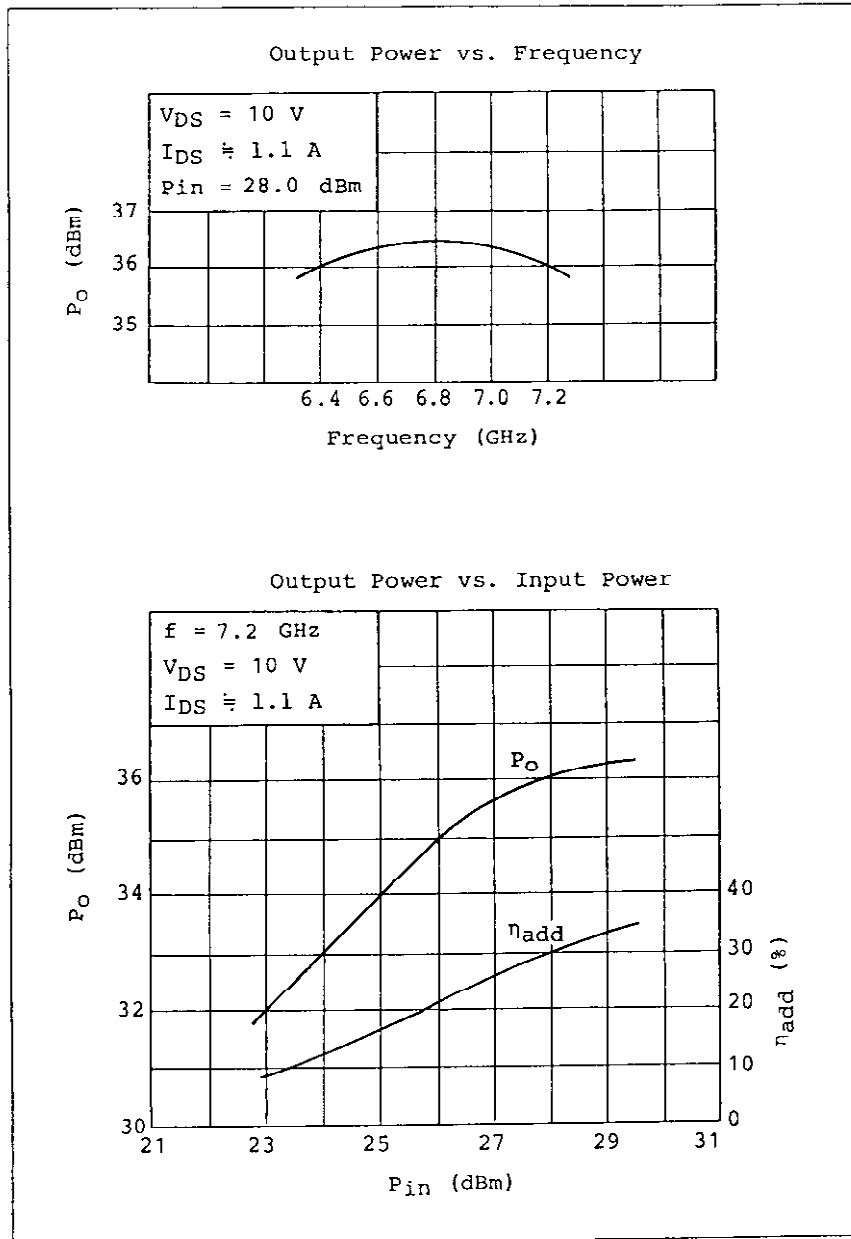
Package Outline (2-11D1B)



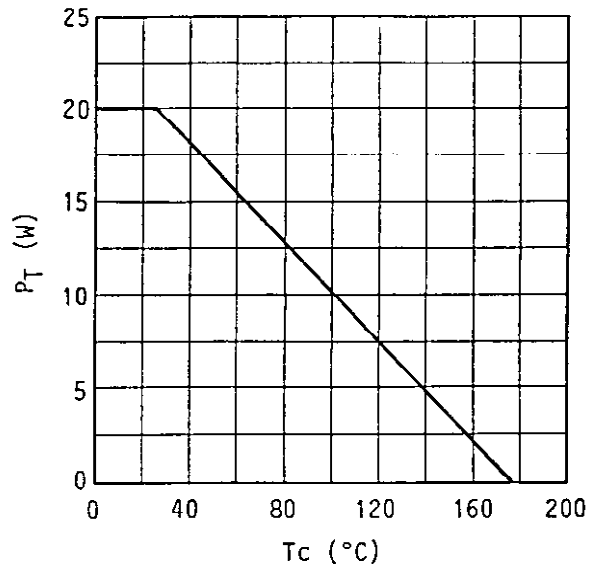
Handling Precautions for Packaged Type

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C.

RF Performances



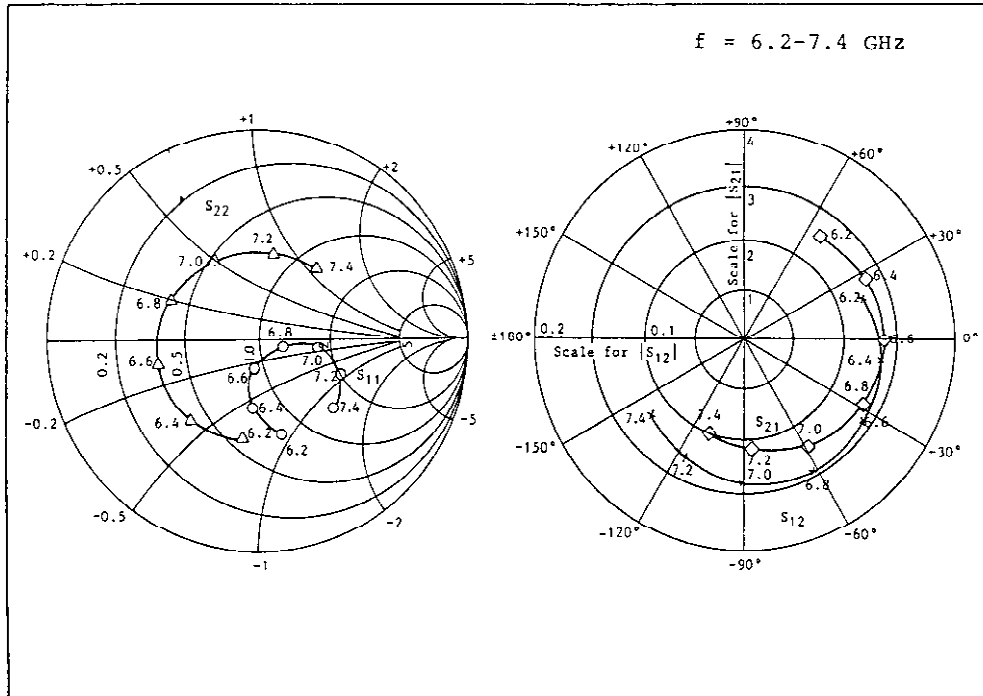
Power Dissipation vs. Case Temperature



TIM6472-4 S-Parameters
(MAGN. and ANGLES)

$V_{DS} = 10 \text{ V}, I_{DS} = 1.0 \text{ A}$

$f = 6.2\text{-}7.4 \text{ GHz}$



FREQUENCY (GHz)	S ₁₁		S ₁₂		S ₂₁		S ₂₂	
6.2	0.46	-78	0.125	20	2.62	55	0.49	-102
6.4	0.32	-97	0.137	-8	2.71	28	0.50	-134
6.6	0.15	-102	0.145	-35	2.75	0	0.50	-166
6.8	0.11	-16	0.148	-63	2.70	-29	0.46	157
7.0	0.28	-9	0.145	-92	2.51	-60	0.43	118
7.2	0.41	-23	0.135	-118	2.26	-86	0.42	80
7.4	0.47	-43	0.124	-141	2.04	-111	0.43	51